

IN THE CLAIMS:

Please amend the claims as follows:

1-6. (Cancelled)

7. (Currently Amended) A silicon single crystal wafer which is a wafer prepared by means of a Czochralski method, the silicon single crystal comprising at least one portion formed of an OSF ring portion in a peripheral region of the silicon single crystal in contact with a boat on which the silicon single crystal is placed for heat treatment.

8. (Previously Presented) A silicon single crystal wafer according to claim 7, wherein the OSF ring region is an annular region with a width of 10 mm or less from a periphery of the silicon single crystal wafer.

9. (Previously Presented) A silicon single crystal wafer according to claim 7, wherein a nitrogen concentration in the silicon single crystal wafer is in the range of 1×10^{10} to $5 \times 10^{15}/\text{cm}^3$.

10. (Previously Presented) A silicon single crystal wafer according to claim 8, wherein a nitrogen concentration in the silicon single crystal wafer is in the range of 1×10^{10} to $5 \times 10^{15}/\text{cm}^3$.

11. (Previously Presented) A manufacturing process for a silicon single crystal wafer comprising the steps of:

growing a silicon single crystal rod by means of a Czochralski method in a condition that an OSF ring region is formed in a peripheral region of the silicon single crystal rod; and slicing the grown silicon single crystal rod into silicon single crystal wafers.

12. (Previously Presented) A manufacturing process for a silicon single crystal wafer according to claim 11, wherein a condition under which the OSF ring region is formed in a peripheral region of the silicon single crystal rod is such that when a pulling rate is indicated by F [mm/min] and an average temperature gradient in a pulling direction in a length between points corresponding to a silicon melting point and 1400°C in the crystal is indicated by G [$^{\circ}\text{C}/\text{mm}$] by definition, there is present in a peripheral region of the crystal, an OSF ring region of a defect distribution chart which shows defect distribution, with an abscissa representing a distance [mm] in a direction to the crystal periphery from the center and an ordinate representing a value of F/G [$\text{mm}^2/^{\circ}\text{C min}$].

13. (Previously Presented) A manufacturing process for a silicon single crystal wafer according to claim 11, wherein when a silicon single crystal rod is grown by means of the Czochralski method, the silicon single crystal rod is pulled while doping the silicon single crystal rod with nitrogen at a concentration in the range of 1×10^{10} to $5 \times 10^{15}/\text{cm}^3$.

14. (Previously Presented) A manufacturing process for a silicon single crystal wafer according to claim 12, wherein when a silicon single crystal rod is grown by means of the

Czochralski method, the silicon single crystal rod is pulled while doping the silicon single crystal rod with nitrogen at a concentration in the range of 1×10^{10} to $5 \times 10^{15}/\text{cm}^3$.